CORRECTION

Correction to: Low-temperature metal-induced crystallization of hydrogenated amorphous $\text{Si}_{1-x}\text{Ge}_x$ ($0.25 \leq x \leq 1$) thin films with Au solution

Shanglong Peng¹ · Xiaoyan Shen¹ · Deyan He¹

Published online: 15 January 2020
© Springer-Verlag GmbH Germany, part of Springer Nature 2019

Correction to: Appl. Phys. A 90, 267–271 (2008) DOI:
<https://doi.org/10.1007/s00339-007-4260-x>

Unfortunately, Fig 6 in the article was incorrect. It should be the AFM image of the $\text{Si}_{1-x}\text{Ge}_x$ ($x=0.5$) film annealed at 350 °C for 3 h. The author cannot prepare the revised figure as his research is focused on other field. Therefore, Fig. 6 and the related contents should be removed or changed as follows.

In the Abstract (p. 267), the first sentence should read as follows:

Low-temperature (~400 °C) metal-induced crystallization of hydrogenated amorphous silicon-germanium thin films using Au solution has been investigated by X-ray diffraction, Raman spectra and scanning electron microscopy.

In the second paragraph in the Introduction (p. 267), the third sentence should read as follows:

X-ray diffraction (XRD), Raman spectra and scanning electron microscopy (SEM) were used to evaluate the structure and morphology of the $\text{Si}_{1-x}\text{Ge}_x$ films.

In the second paragraph in the Experimental details (p. 268), the first sentence should read as follows:

The structure and the morphology of the samples were characterized with XRD, Raman spectra and SEM measurements.

In the Results and discussion (p. 269), the sixth paragraph and Fig. 6 (p. 270) should be removed. Because of that Fig. 7 and Fig. 8 (also their citations) should be changed to Fig. 6 and Fig. 7 respectively.

In the first paragraph in the Conclusions (p. 270), the sixth sentence “The roughness of the surface of the films is as low as 4.2 nm.” should be removed.

The original article can be found online at <https://doi.org/10.1007/s00339-007-4260-x>.

✉ Deyan He
hedy@lzu.edu.cn

¹ Department of Physics, Lanzhou University,
Lanzhou 730000, P.R. China